

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Ryoji HOSHI et al.

Application No.: New U.S. National Stage of PCT/JP03/11443

Filed: February 22, 2005

Docket No.: 122810

For: SINGLE CRYSTAL, SINGLE CRYSTAL WAFER, EPITAXIAL WAFER, AND  
METHOD OF GROWING SINGLE CRYSTAL

PRELIMINARY AMENDMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Please consider the following:

**Amendments to the Claims** as reflected in the listing of claims;

**Remarks.**